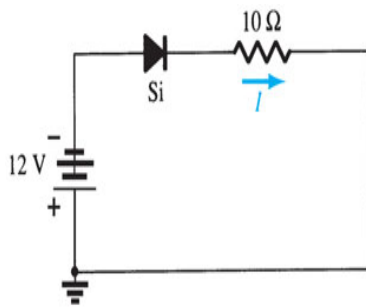


## **TUTORIAL SHEET NO. 1**

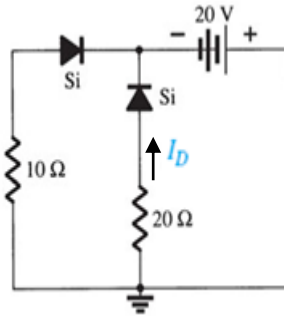
### **(Diode Equation, Effect of temperature on reverse current, diode resistance)**

- Q1. The current flowing in diode is  $2 \times 10^{-7} \text{A}$  at room temperature when a reverse voltage is applied. Calculate current through diode when a forward bias of 0.1V is applied across diode at room temperature. *Answer:  $1.16 \mu\text{A}$*
- Q2. At room temperature current flowing in a p-n diode is 0.5mA at 340mV and 15mA at 440mV. Calculate value of  $\eta$  for the same. *Answer: 1.1*
- Q3. A germanium diode carries a current of 1mA at room temperature when a forward bias of 0.15V is applied. Calculate reverse current for the same. *Answer:  $3.13 \mu\text{A}$*
- Q4. Find the increase in temperature necessary to increase reverse current by a factor of 100. *Answer:  $66.4^\circ\text{C}$*
- Q5. For what diode terminal voltage the reverse current of a Ge diode reach 99% of its saturation value at  $300^\circ\text{K}$  temperature. *Answer:  $-0.119\text{V}$*
- Q6. At room temperature current through a germanium diode is 5mA at 0.35V. Predict the diode current if applied voltage is 0.4V. *Answer:  $34.19\text{mA}$*
- Q7. Find increase in forward bias voltage that doubles the forward current through a silicon diode at room temperature. *Answer:  $36.04\text{mV}$*
- Q8. An ideal Ge diode at a temperature of  $125^\circ\text{C}$  has a reverse saturation current of  $30 \mu\text{A}$ . Calculate dynamic resistance for a 0.2V bias (i) Forward bias (ii) Reverse bias condition. *Answer:  $3.36\Omega$ ,  $0.389\text{M}\Omega$*
- Q9. Find the static and dynamic resistance of a Ge diode if the temperature is  $27^\circ\text{C}$  and reverse saturation current is  $1 \mu\text{A}$  for an applied forward bias of 0.2V. *Answer:  $91.32\Omega$ ,  $11.86\Omega$*
- Q10. Determine the diode current at  $20^\circ\text{C}$  for a silicon diode with  $I_s = 50 \text{ nA}$  and an applied forward bias of 0.6 V. *Answer:  $8.13\text{mA}$*

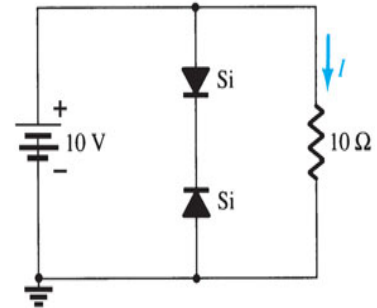
Q11. Determine the current  $I$  for each of the configurations using the approximate equivalent model for the diode.



Answer: 0A

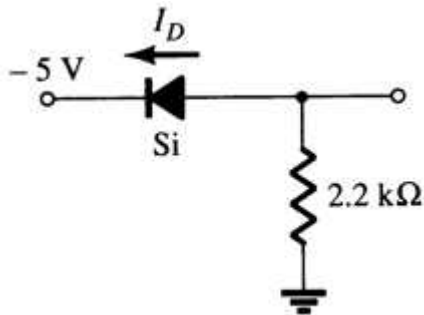


Answer: 0.965A

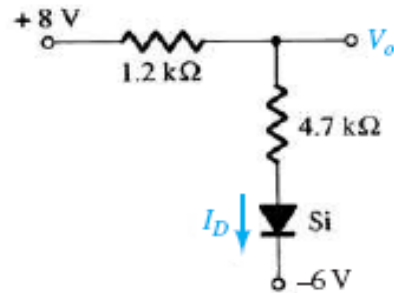


Answer: 1A

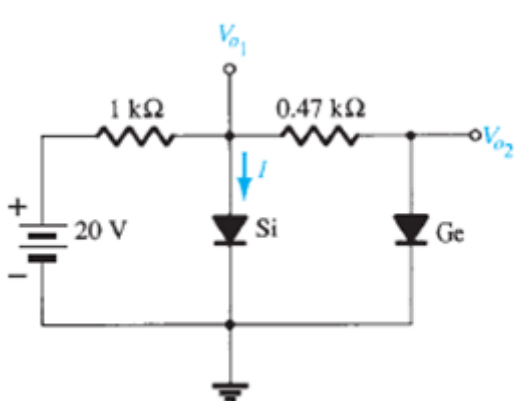
Q12. Determine  $V_o$  and  $I_D$  for the networks



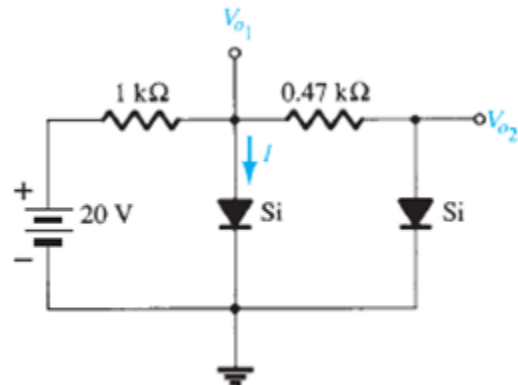
Answer: -4.3V, 1.95mA



Answer: 5.3V, 2.25mA

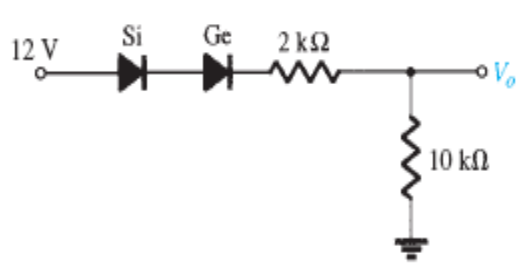


Answer: 0.7V, 0.3V, 18.45mA

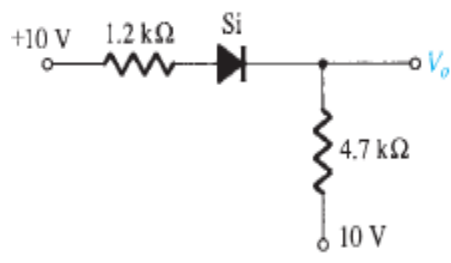


Answer: 0.7V, 0.7V, 19.3mA

Q13. Determine the level of  $V_o$

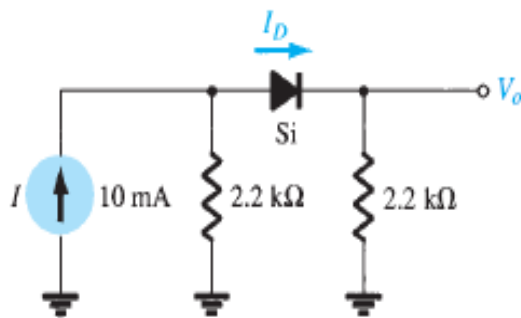


Answer: 9.17V

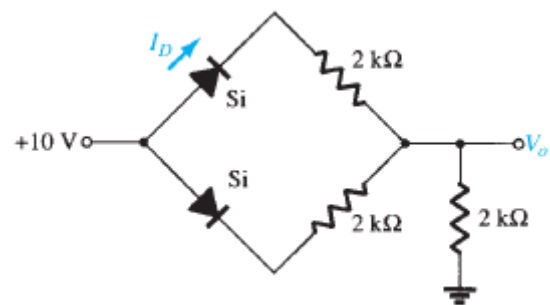


Answer: 10V

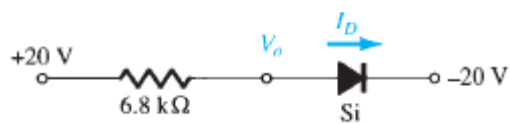
Q14. Determine  $V_o$  and  $I_D$  for the networks.



Answer: 7.512V, 6.26mA

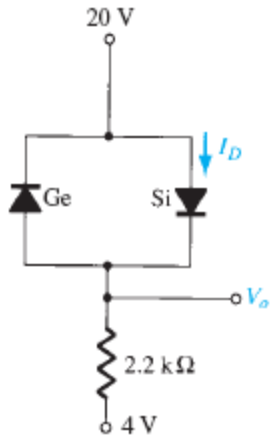


Answer: 7.14V, 1.55mA

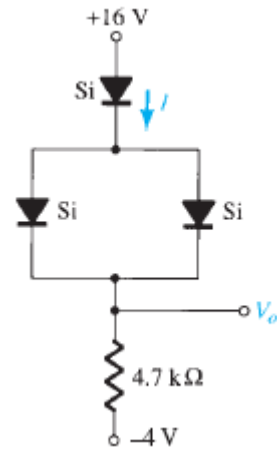


Answer: -19.3V, 5.77mA

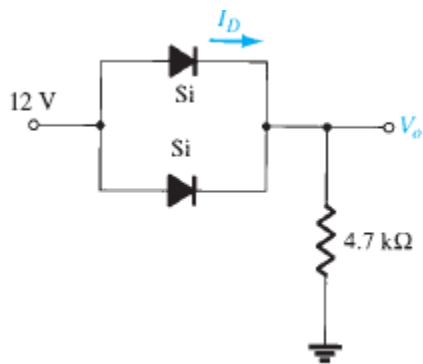
Q15. Determine  $V_o$  and  $I_D$  for the networks



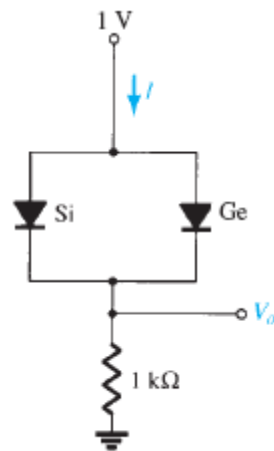
Answer: 19.3V, 6.95mA



Answer: 14.6V, 3.957mA



Answer: 11.3V, 2.4mA



Answer: 0.7V, 0.7mA